Central™
Semiconductor Corp.

PROCESS CP289

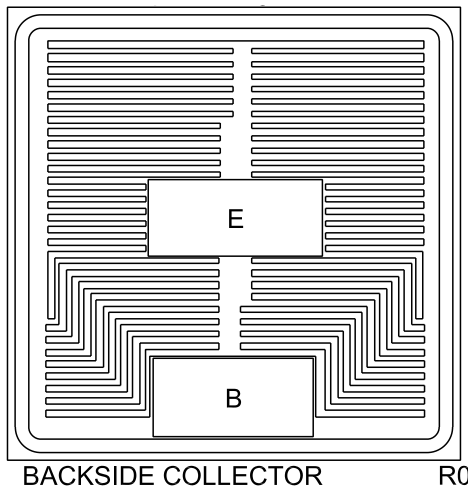
Power Transistors

8.0 Amp NPN - High Voltage Transistor Chip

PROCESS DETAILS

Die Size	167 x 167 MILS
Die Thickness	9.5 MILS
Base Bonding Pad Area	59 x 29 MILS
Emitter Bonding Pad Area	64 x 28 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Ti/Ni/Ag - 3,000Å, 10,000Å, 10,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER
558

PRINCIPAL DEVICE TYPES
MJE13009

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R0 (5- January 2006)